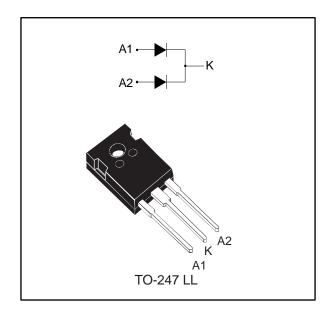
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STPSC40H12C

1200 V power Schottky silicon carbide diode

Datasheet - production data



Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- Operating T_j from -40 °C to 175 °C
- ECOPACK®2 compliant

Description

The SiC diode, available in TO-247 LL, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low V_F Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC and secondary side applications, this ST SiC diode will boost the performance in hard switching conditions. This rectifier will enhance the performance of the targeted application. Its high forward surge capability ensures a good robustness during transient phases.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 20 A
V_{RRM}	1200 V
T _j (max.)	175 °C
V _F (typ.)	1.35 V

Characteristics STPSC40H12C

1 Characteristics

Table 2: Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol		Value	Unit			
V _{RRM}	Repetitive peak reverse	voltage ($T_j = -40 ^{\circ}\text{C}$ to +175	°C)	1200	V	
I _{F(RMS)}	Forward rms current			38	Α	
		T _C = 150 °C, DC current		20/40		
I _{F(AV)}	Average forward current	T _C = 135 °C, DC current	Per diode/per device	27/54	Α	
	Garroni	T _C = 25 °C, DC current		38/76		
I _{FRM}	Repetitive peak forward current	T _C = 150 °C, T _j = 175 °C, δ = 0.1		79	Α	
	_	t 10 ma ainuacidal	T _C = 25 °C	140		
I _{FSM}	I _{FSM} Surge non repetitive forward current	t _p = 10 ms sinusoidal	T _C = 150 °C	120	Α	
Torward barront		$t_p = 10 \ \mu s \ square$ $T_C = 25 \ ^{\circ}C$		700		
T _{stg}	Storage temperature ran	-65 to +175	°C			
Tj	Operating junction temperature range -40 to				°C	

Table 3: Thermal resistance parameters

Symbol	Parameter		Typ. value	Max. value	Unit
Р	lunation to acco	Per diode	0.40	0.55	°C/W
R _{th(j-c)}	Junction to case	Per device	0.20	0.28	C/VV

Table 4: Static electrical characteristics (per diode)

;	Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
	I _R ⁽¹⁾	Devenue le des un summer	T _j = 25 °C	$V_R = V_{RRM}$	-	10	120	μΑ
	Reverse leakage	Reverse leakage current	T _j = 150 °C		-	60	800	
	V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I- 20 A	1	1.35	1.50	V
			T _j = 150 °C	I _F = 20 A	-	1.75	2.25	\ \

Notes:

 $^{(1)}$ Pulse test: t_p = 10 ms, δ < 2%

(2) Pulse test: $t_p = 500 \ \mu s, \ \delta < 2\%$

To evaluate the conduction losses, use the following equation:

 $P = 1.07 \text{ x } I_{F(AV)} + 0.059 \text{ x } I_{F^{2}(RMS)}$

STPSC40H12C Characteristics

Table 5: Dynamic electrical characteristics (per diode)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Qcj ⁽¹⁾	Total capacitive charge	V _R = 800 V	-	129	1	nC
0	Total conscitores	$V_R = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ MHz}$	-	1650	-	
Cj	Total capacitance	V _R = 800 V, T _c = 25 °C, F = 1 MHz	-	110	-	pF

Notes:

⁽¹⁾Most accurate value for the capacitive charge: $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$

Characteristics STPSC40H12C

1.1 Characteristics (curves)

Figure 1: Forward voltage drop versus forward

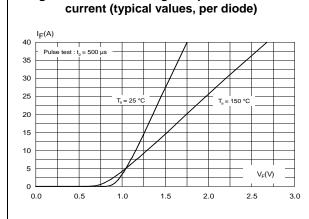


Figure 2: Reverse leakage current versus reverse voltage applied (typical values, per diode)

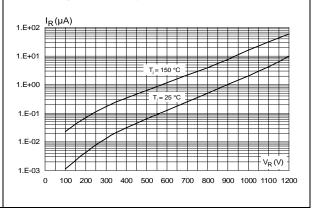


Figure 3: Peak forward current versus case temperature (per diode)

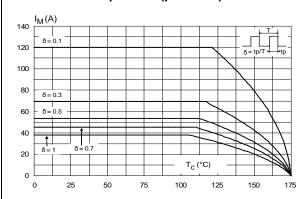


Figure 4: Junction capacitance versus reverse voltage applied (typical values, per diode)

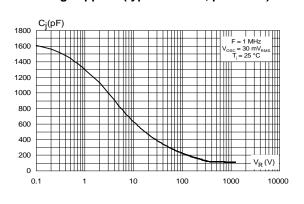


Figure 5: Relative variation of thermal impedance junction to case versus pulse duration

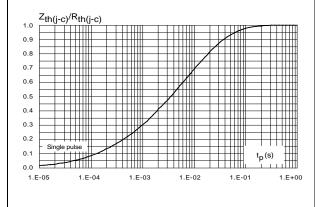
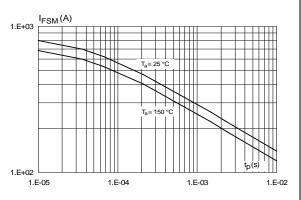
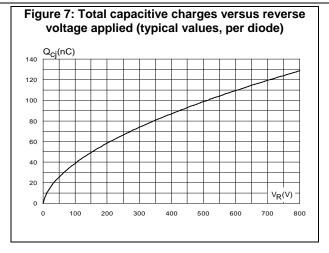


Figure 6: Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform, per diode)



STPSC40H12C Characteristics



Package information STPSC40H12C

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.9 to 1.2 N·m

STPSC40H12C Package information

2.1 TO-247 long leads package information

Figure 8: TO-247 long leads package outline

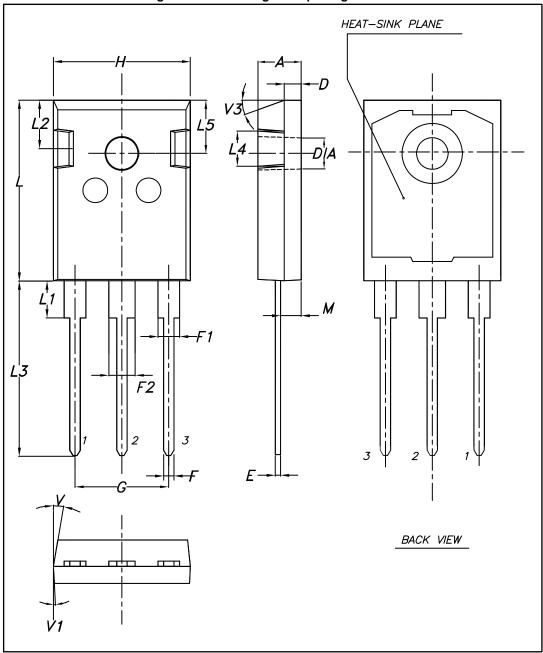


Table 6: TO-247 long leads package mechanical data

	mm.			mm. Inches		
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.90		5.15	0.192		0.202
D	1.85		2.10	0.072		0.082
Е	0.55		0.67	0.021		0.026
F	1.07		1.32	0.042		0.051
F1	1.90		2.38	0.074		0.093
F2	2.87		3.38	0.110		0.133
G	10.90 BSC				0.429 BSC	
Н	15.77		16.02	0.620		0.630
L	20.82		21.07	0.810		0.820
L1	4.16		4.47	0.163		0.175
L2	5.49		5.74	0.216		0.225
L3	20.05		20.30	0.789		0.799
L4	3.68		3.93	0.144		0.154
L5	6.04		6.29	0.237		0.247
М	2.25		2.55	0.088		0.100
V		10°			10°	
V1		3°			3°	
V3		20°			20°	
DIA	3.55		3.66	0.139		0.143

STPSC40H12C Ordering information

3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC40H12CWL	STPSC40H12CWL	TO-247 LL	6.09 g	30	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
28-Feb-2017	1	Initial release.

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